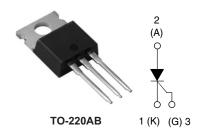




Vishay High Power Products

### Phase Control SCR, 25 A



PRODUCT SUMMARY				
V <sub>T</sub> at 16 A < 1.25 V				
I <sub>TSM</sub>	300 A			
$V_{RRM}$	800/1200 V			

#### **DESCRIPTION/FEATURES**

The 25TTS... High Voltage Series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

Typical applications are in input rectification (soft start) and these products are designed to be used with Vishay HPP input diodes, switches and output rectifiers which are available in identical package outlines.

This product has been designed and qualified for industrial level.

OUTPUT CURRENT IN TYPICAL APPLICATIONS					
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS		
Capacitive input filter T <sub>A</sub> = 55 °C, T <sub>J</sub> = 125 °C, common heatsink of 1 °C/W	18	22	А		

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
I <sub>T(AV)</sub>	Sinusoidal waveform	16	Λ		
I <sub>RMS</sub>		25	Α		
V <sub>RRM</sub> /V <sub>DRM</sub>		800/1200	V		
I <sub>TSM</sub>		300	А		
V <sub>T</sub>	16 A, T <sub>J</sub> = 25 °C	1.25	V		
dV/dt		500	V/µs		
dl/dt		150	A/μs		
TJ		- 40 to 125	°C		

VOLTAGE RATINGS						
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM PEAK DIRECT VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 °C mA			
25TTS08	800	800	10			
25TTS12	1200	1200	10			

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# 25TTS... High Voltage Series

## Vishay High Power Products Phase Control SCR, 25 A



ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST COMPITIONS		VALUES		
PARAMETER	SYMBOL TEST CONDITIONS		NUTTIONS	TYP.	MAX.	UNITS
Maximum average on-state current	I <sub>T(AV)</sub>	T <sub>C</sub> = 93 °C, 180° conduc	tion half sine wave	16		
Maximum RMS on-state current	I <sub>RMS</sub>			2	5	Α
Maximum peak, one-cycle,	I	10 ms sine pulse, rated	V <sub>RRM</sub> applied	30	00	_ ^
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse, no vol	tage reapplied	3	50	
Maximum I <sup>2</sup> t for fusing	l <sup>2</sup> t	10 ms sine pulse, rated	V <sub>RRM</sub> applied	450		A <sup>2</sup> s
Maximum i-t for fusing	I <del>-</del> t	10 ms sine pulse, no voltage reapplied		630		A-S
Maximum I <sup>2</sup> √t for fusing	I <sup>2</sup> √t	t = 0.1 to 10 ms, no voltage reapplied		63	00	A²√s
Maximum on-state voltage drop	$V_{TM}$	16 A, T <sub>J</sub> = 25 °C		1.	25	V
On-state slope resistance	r <sub>t</sub>	T _ 105 °C		12	2.0	mΩ
Threshold voltage	$V_{T(TO)}$	- T <sub>J</sub> = 125 °C		1	.0	V
Maximum rayarea and direct lookage current	1 /1	T <sub>J</sub> = 25 °C	V - Potod V /V	0.5		
Maximum reverse and direct leakage current	I <sub>RM</sub> /I <sub>DM</sub>	$V_R = Rated V_{RRM}/V_{DRM}$		1	0	mA
Holding current	l <sub>Η</sub>	Anode supply = 6 V, resistive load, initial $I_T = 1 A$		-	100	IIIA
Maximum latching current	IL	Anode supply = 6 V, resistive load		20	00	
Maximum rate of rise of off-state voltage	dV/dt			50	00	V/µs
Maximum rate of rise of turned-on current	dl/dt			1	50	A/μs

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	$P_{GM}$		8.0	W	
Maximum average gate power	$P_{G(AV)}$		2.0	VV	
Maximum peak positive gate current	+ I <sub>GM</sub>		1.5	Α	
Maximum peak negative gate voltage	- V <sub>GM</sub>		10	V	
Maximum required DC gate current to trigger	I <sub>GT</sub>	Anode supply = 6 V, resistive load, T <sub>J</sub> = - 10 °C	60	mA	
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	45		
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	20		
Maximum required DC gate voltage to trigger	$V_{\mathrm{GT}}$	Anode supply = 6 V, resistive load, T <sub>J</sub> = - 10 °C	2.5		
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	2.0	V	
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	1.0	V	
Maximum DC gate voltage not to trigger	$V_{GD}$	T = 105 °C V = Poted volue	0.25		
Maximum DC gate current not to trigger	$I_{GD}$	T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = Rated value		mA	

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.9	
Typical reverse recovery time	t <sub>rr</sub>	T - 105 °C	4	μs
Typical turn-off time	t <sub>q</sub>	T <sub>J</sub> = 125 °C	110	



## 25TTS... High Voltage Series

# Phase Control SCR, 25 A Vishay High Power Products

THERMAL AND MEC	HANICAL	SPECIFIC	CATIONS		
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range		T <sub>J</sub> , T <sub>Stg</sub>		- 40 to 125	°C
Maximum thermal resistance, junction to case		R <sub>thJC</sub>	DC operation	1.1	
Maximum thermal resistance, junction to ambient		R <sub>thJA</sub>		62	°C/W
Typical thermal resistance, case to heatsink		R <sub>thCS</sub>	Mounting surface, smooth and greased	0.5	
Approximate weight				2	g
Approximate weight				0.07	OZ.
Mounting torque ————	minimum			6 (5)	kgf · cm
	maximum			12 (10)	(lbf ⋅ in)
Marking device			Case style TO-220AB	25T	TS08
				25T	ΓS12

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### Vishay High Power Products Phase Control SCR, 25 A



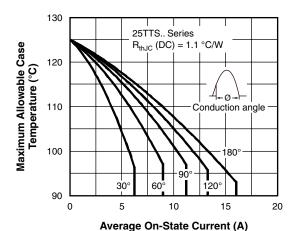


Fig. 1 - Current Rating Characteristics

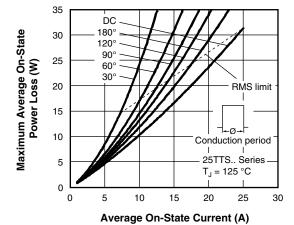


Fig. 4 - On-State Power Loss Characteristics

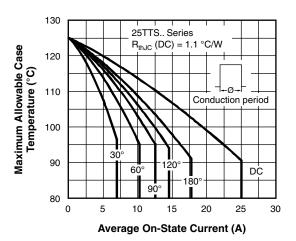
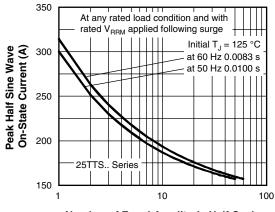


Fig. 2 - Current Rating Characteristics



Number of Equal Amplitude Half Cycle Current Pulses (N)

Fig. 5 - Maximum Non-Repetitive Surge Current

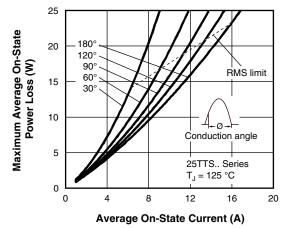


Fig. 3 - On-State Power Loss Characteristics

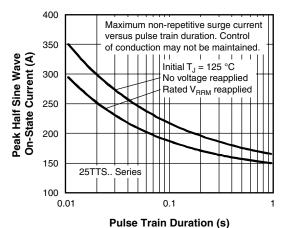


Fig. 6 - Maximum Non-Repetitive Surge Current



## Phase Control SCR, 25 A Vishay High Power Products

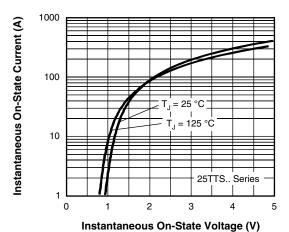


Fig. 7 - On-State Voltage Drop Characteristics

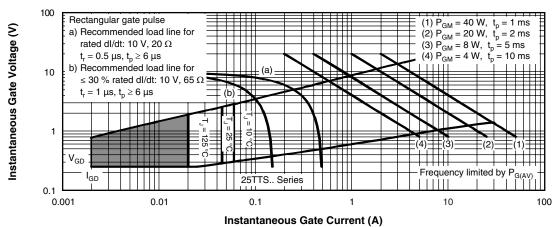


Fig. 8 - Gate Characteristics

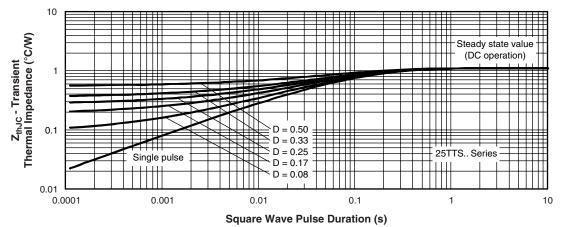


Fig. 9 - Thermal Impedance  $Z_{thJC}$  Characteristics

## 25TTS... High Voltage Series

Vishay High Power Products Phase Control SCR, 25 A



#### **ORDERING INFORMATION TABLE**

Device code 25 T T S 12 -

1 - Current rating (25 = 25 A)

2 - Circuit configuration:

T = Single thyristor

3 - Package:

T = TO-220AB

4 - Type of silicon:

S = Standard recovery rectifier

08 = 800 V

12 = 1200 V

5 - Voltage rating —————

- • None = Standard production

• PbF = Lead (Pb)-free

LINKS TO RELATED DOCUMENTS				
Dimensions http://www.vishay.com/doc?95222				
Part marking information	http://www.vishay.com/doc?95225			

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